<u>MOSFET</u> – Single, P-Channel, Small Signal, Gate Zener, SC-75, SC-89

-20 V, -760 mA

Features

- Low R_{DS(on)} for Higher Efficiency and Longer Battery Life
- Small Outline Package (1.6 x 1.6 mm)
- SC-75 Standard Gullwing Package
- ESD Protected Gate
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- High Side Load Switch
- DC-DC Conversion
- Small Drive Circuits
- Battery Operated Systems such as Cell Phones, PDAs, Digital Cameras, etc.

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Value	Units	
Drain-to-Source Voltage	V _{DSS}	-20	V	
Gate-to-Source Voltage	V _{GS}	±6.0	V	
Continuous Drain Current (Note 1)	۱ _D	-760	mA	
Power Dissipation (Note 1) SC-75 SC-89	SC–75 Steady State		301 313	mW
Pulsed Drain Current	I _{DM}	±1000	mA	
Operating Junction and Storage	T _J , T _{STG}	–55 to 150	°C	
Continuous Source Current (Bo	ody Diode)	۱ _S	-250	mA
Lead Temperature for Soldering (1/8 in from case for 10 s)	ΤL	260	°C	
Gate-to-Source ESD Rating - (Human Body Model)	, Method 3015)	ESD	1800	V

THERMAL RESISTANCE RATINGS

Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$		°C/W
SC-75		415	
SC-89		400	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

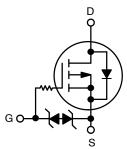


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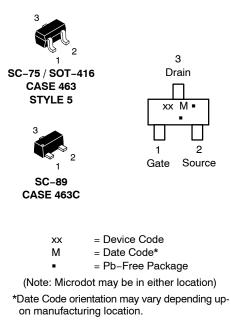
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V _{(BR)DSS}	R _{DS(on)} TYP	I _D MAX
-20 V	0.26 Ω @ –4.5 V	
	0.35 Ω @ –2.5 V	–760 mA
	0.49 Ω @ –1.8 V	





MARKING DIAGRAM & PIN ASSIGNMENT



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_{.1} = 25°C unless otherwise stated)

Parameter Symbol Test Condition				Тур	Max	Unit
OFF CHARACTERISTICS			•			
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V_{GS} = 0 V, I_D = -250 μ A	-20			V
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V, V_{DS} = -16 V$	V _{GS} = 0 V, V _{DS} = -16 V		-100	nA
Gate-to-Source Leakage Current	I _{GSS}	V_{DS} = 0 V, V_{GS} = ±4.5 V		±1.0	±10	μA
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	V _{GS(TH)}	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$ -0.45			-1.2	V
Drain-to-Source On Resistance	R _{DS(on)}	V_{GS} = -4.5 V, I _D = -350 mA		0.26	0.36	Ω
		V_{GS} = -2.5 V, I _D = -300 mA		0.35	0.45	
		$V_{GS} = -1.8 \text{ V}, \text{ I}_{D} = -150 \text{ mA}$		0.49	1.0	
Forward Transconductance	9 FS	V _{DS} = -10 V, I _D = -250 mA		0.4		S
CHARGES AND CAPACITANCES						
Input Capacitance	C _{ISS}	$V_{GS} = 0 V, f = 1.0 MHz,$		156		pF
Output Capacitance	C _{OSS}	V _{DS} = -5.0 V		28		
Reverse Transfer Capacitance	C _{RSS}			18		
Total Gate Charge	Q _{G(TOT)}	$V_{GS} = -4.5 \text{ V}, V_{DD} = -10 \text{ V},$		2.1		nC
Threshold Gate Charge	Q _{G(TH)}	$I_{\rm D} = -0.3$ Å		0.125		
Gate-to-Source Charge	Q _{GS}			0.325		
Gate-to-Drain Charge	Q _{GD}			0.5		
SWITCHING CHARACTERISTICS (Note	3)	• •				
Turn-On Delay Time	td _(ON)	$V_{GS} = -4.5 \text{ V}, V_{DD} = -10 \text{ V},$		8.0		ns
Rise Time	t _r	I_D = -200 mA, R_G = 10 Ω		8.2		
Turn-Off Delay Time	td _(OFF)			29		
Fall Time	t _f			20.4		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V_{GS} = 0 V, I _S = -250 mA		-0.72	-1.1	V	
Developt assessmentic assessments is indicated in the Electrical Observatoristics for the listed text conditions, unlarge athematics parted. Developt							

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: pulse width \leq 300 μ s, duty cycle \leq 2%.

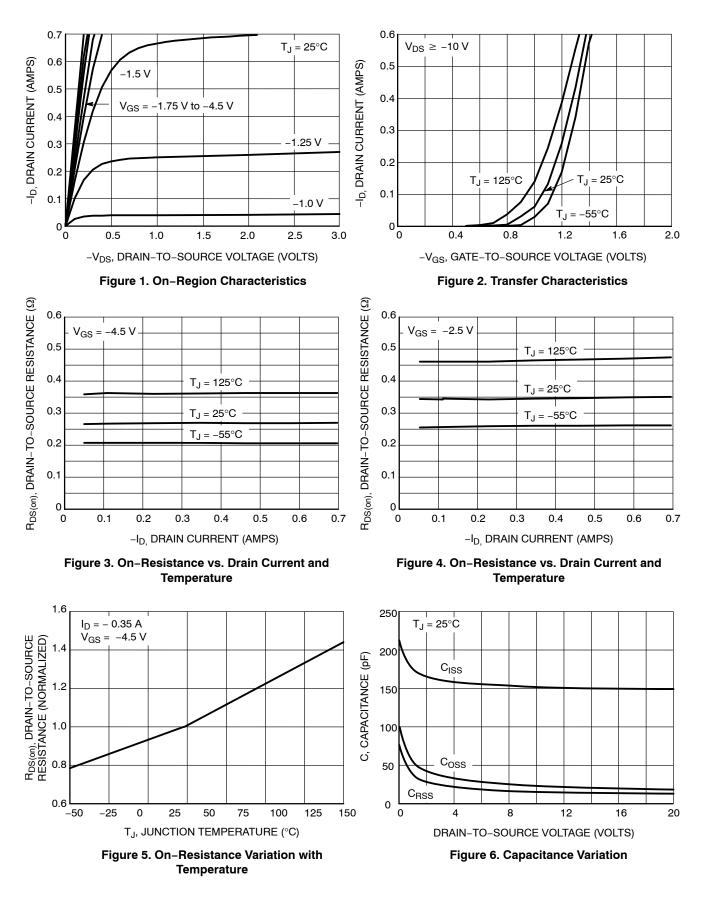
3. Switching characteristics are independent of operating junction temperatures.

ORDERING INFORMATION

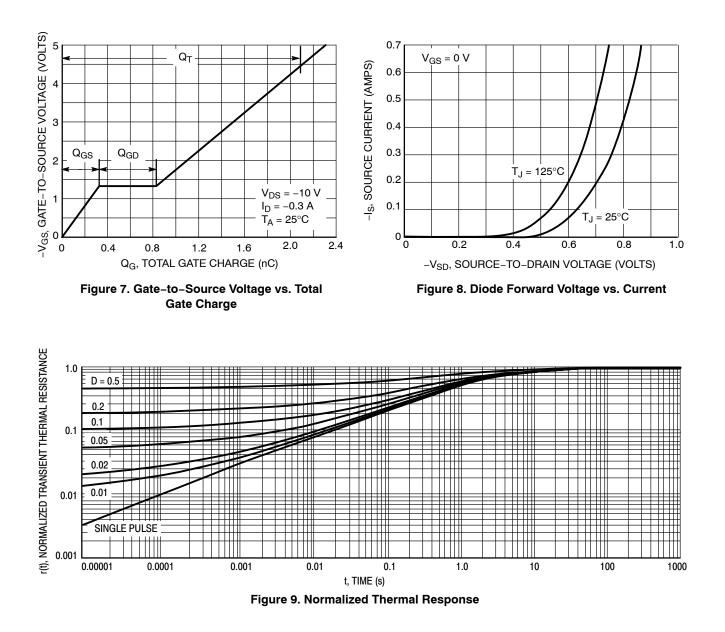
Device	Marking	Package	Shipping [†]
NTA4151PT1G	TN	SC-75 (Pb-Free)	3000 / Tape & Reel
NTE4151PT1G	ТМ	SC–89 (Pb–Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL ELECTRICAL CHARACTERISTICS

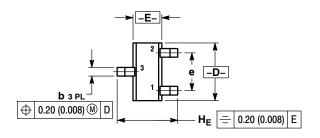


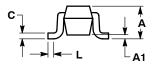
TYPICAL ELECTRICAL CHARACTERISTICS



PACKAGE DIMENSIONS

SC-75/SOT-416 **CASE 463 ISSUE F**



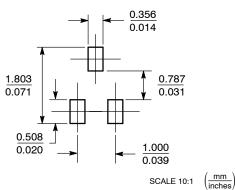


NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

	MIL	LIMETE	RS	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.70	0.80	0.90	0.027	0.031	0.035	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
b	0.15	0.20	0.30	0.006	0.008	0.012	
С	0.10	0.15	0.25	0.004	0.006	0.010	
D	1.55	1.60	1.65	0.059	0.063	0.067	
Е	0.70	0.80	0.90	0.027	0.031	0.035	
е	1	.00 BSC		0.04 BSC			
L	0.10	0.15	0.20	0.004	0.006	0.008	
HE	1.50	1.60	1.70	0.061	0.063	0.065	

STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

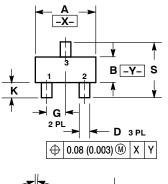
SOLDERING FOOTPRINT*

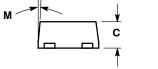


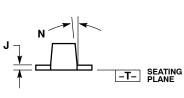
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SC-89, 3-LEAD CASE 463C-03 **ISSUE C**





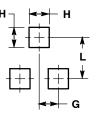


NOTES DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

- З.
- CONTROLLING DIMENSION: MILLIMETERS MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 463C-01 OBSOLETE, NEW STANDARD 463C-02.

	MILLIMETERS			MILLIMETERS INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	1.50	1.60	1.70	0.059	0.063	0.067	
В	0.75	0.85	0.95	0.030	0.034	0.040	
c	0.60	0.70	0.80	0.024	0.028	0.031	
D	0.23	0.28	0.33	0.009	0.011	0.013	
G	0.50 BSC			0.020 BSC			
Η	0.53 REF			0	.021 RE	F	
L	0.10	0.15	0.20	0.004	0.006	0.008	
K	0.30	0.40	0.50	0.012	0.016	0.020	
L	1	1.10 REF			0.043 REF		
М			10			10	
Ν			10 -			10 -	
S	1.50	1.60	1.70	0.059	0.063	0.067	

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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